

7MBP300RA060

IGBT-IPM R series

600V / 300A 7 in one-package

Features

- Temperature protection provided by directly detecting the junction temperature of the IGBTs
- Low power loss and soft switching
- High performance and high reliability IGBT with overheating protection
- Higher reliability because of a big decrease in number of parts in built-in control circuit



Maximum ratings and characteristics

- Absolute maximum ratings(at $T_c=25^\circ\text{C}$ unless otherwise specified)

| Item | Symbol | Rating | | Unit | |
|--|-----------------|----------|----------|-------------------|-----|
| | | Min. | Max. | | |
| DC bus voltage | V_{DC} | 0 | 450 | V | |
| DC bus voltage (surge) | $V_{DC(surge)}$ | 0 | 500 | V | |
| DC bus voltage (short operating) | V_{SC} | 200 | 400 | V | |
| Collector-Emitter voltage | V_{CES} | 0 | 600 | V | |
| DB Reverse voltage | V_R | - | 600 | V | |
| INV Collector current | DC | I_C | - | 300 | A |
| | 1ms | I_{CP} | - | 600 | A |
| | Duty=55.5% | $-I_C$ | - | 300 | A |
| Collector power dissipation | One transistor | P_C | - | 1040 | W |
| DB Collector current | DC | I_C | - | 100 | A |
| | 1ms | I_{CP} | - | 200 | A |
| Forward current of Diode | | I_F | - | 100 | A |
| Collector power dissipation | One transistor | P_C | - | 400 | W |
| Junction temperature | T_j | - | 150 | $^\circ\text{C}$ | |
| Input voltage of power supply for Pre-Driver | V_{CC}^*1 | 0 | 20 | V | |
| Input signal voltage | V_{in}^*2 | 0 | V_Z | V | |
| Input signal current | I_{in} | - | 1 | mA | |
| Alarm signal voltage | V_{ALM}^*3 | 0 | V_{CC} | V | |
| Alarm signal current | I_{ALM}^*4 | - | 15 | mA | |
| Storage temperature | T_{stg} | -40 | 125 | $^\circ\text{C}$ | |
| Operating case temperature | T_{op} | -20 | 100 | $^\circ\text{C}$ | |
| Isolating voltage (Case-Terminal) | V_{iso}^*5 | - | AC2.5 | kV | |
| Screw torque | Mounting (M5) | | - | 3.5 ^{*6} | N·m |
| | Terminal (M5) | | - | 3.5 ^{*6} | N·m |

*1 Apply V_{CC} between terminal No. 3 and 1, 6 and 4, 9 and 7, 11 and 10.

*2 Apply V_{in} between terminal No. 2 and 1, 5 and 4, 8 and 7, 12,13,14,15 and 10.

*3 Apply V_{ALM} between terminal No. 16 and 10.

*4 Apply I_{ALM} to terminal No. 16.

*5 50Hz/60Hz sine wave 1 minute.

*6 Recommendable Value : 2.5 to 3.0 N·m

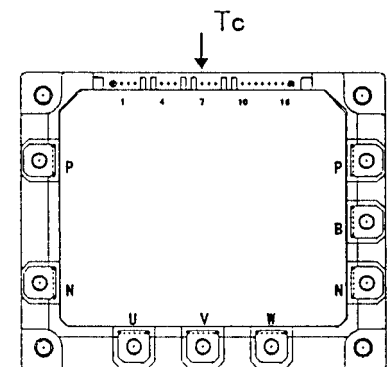


Fig.1 Measurement of case temperature

- Electrical characteristics of power circuit (at $T_c=T_j=25^\circ\text{C}$, $V_{CC}=15\text{V}$)

| Item | Symbol | Condition | Min. | Typ. | Max. | Unit | |
|------|---------------------------------------|---------------|--|------|------|------|----|
| INV | Collector current at off signal input | I_{CES} | $V_{CE}=600\text{V}$ input terminal open | - | - | 1.0 | mA |
| | Collector-Emitter saturation voltage | $V_{CE(sat)}$ | $I_C=300\text{A}$ | - | - | 2.8 | V |
| | Forward voltage of FWD | V_F | $-I_C=300\text{A}$ | - | - | 3.0 | V |
| DB | Collector current at off signal input | I_{CES} | $V_{CE}=600\text{V}$ input terminal open | - | - | 1.0 | mA |
| | Collector-Emitter saturation voltage | $V_{CE(sat)}$ | $I_C=100\text{A}$ | - | - | 2.8 | V |
| | Forward voltage of Diode | V_F | $-I_C=100\text{A}$ | - | - | 3.0 | V |

● Electrical characteristics of control circuit(at $T_c=T_j=25^\circ\text{C}$, $V_{cc}=15\text{V}$)

| Item | Symbol | Condition | Min. | Typ. | Max. | Unit | |
|--|--------------|--|-------------------------|------|------|------------------|---|
| Power supply current of P-line side Pre-driver(one unit) | I_{ccp} | $f_{sw}=0$ to 15kHz $T_c=-20$ to 100°C *7 | 6 | - | 32 | mA | |
| Power supply current of N-line side three Pre-driver | I_{ccn} | $f_{sw}=0$ to 15kHz $T_c=-20$ to 100°C *7 | 24 | - | 114 | mA | |
| Input signal threshold voltage (on/off) | $V_{in(th)}$ | ON | 1.00 | 1.35 | 1.70 | V | |
| | | OFF | 1.70 | 2.05 | 2.40 | V | |
| Input zener voltage | V_z | $R_{in}=20\text{k ohm}$ | - | 8.0 | - | V | |
| Over heating protection temperature level | T_{COH} | $V_{DC}=0\text{V}$, $I_c=0\text{A}$, Case temperature, Fig.1 | 110 | - | 125 | $^\circ\text{C}$ | |
| Hysteresis | T_{CH} | | - | 20 | - | $^\circ\text{C}$ | |
| IGBT chips over heating protection temperature level | T_{jOH} | surface of IGBT chips | 150 | - | - | $^\circ\text{C}$ | |
| Hysteresis | T_{jH} | | - | 20 | - | $^\circ\text{C}$ | |
| Collector current protection level | INV | I_{oc} | $T_j=125^\circ\text{C}$ | 450 | - | - | A |
| | DB | I_{oc} | $T_j=125^\circ\text{C}$ | 150 | - | - | A |
| Over current protection delay time (Fig.2) | t_{DOC} | $T_j=25^\circ\text{C}$ Fig.2 | - | 10 | - | μs | |
| Under voltage protection level | V_{UV} | | 11.0 | - | 12.5 | V | |
| Hysteresis | V_H | | 0.2 | - | - | V | |
| Alarm signal hold time | t_{ALM} | | 1.5 | 2 | - | ms | |
| SC protection delay time | t_{SC} | $T_j=25^\circ\text{C}$ Fig.3 | - | - | 12 | μs | |
| Limiting resistor for alarm | R_{ALM} | | 1425 | 1500 | 1575 | ohm | |

*7 Switching frequency of IPM

● Dynamic characteristics(at $T_c=T_j=125^\circ\text{C}$, $V_{cc}=15\text{V}$)

| Item | Symbol | Condition | Min. | Typ. | Max. | Unit |
|-----------------------|-----------|--|------|------|------|---------------|
| Switching time (IGBT) | t_{on} | $I_C=300\text{A}$, $V_{DC}=300\text{V}$ | 0.3 | - | - | μs |
| | t_{off} | | - | - | 3.6 | μs |
| Switching time (FWD) | t_{rr} | $I_F=300\text{A}$, $V_{DC}=300\text{V}$ | - | - | 0.4 | μs |

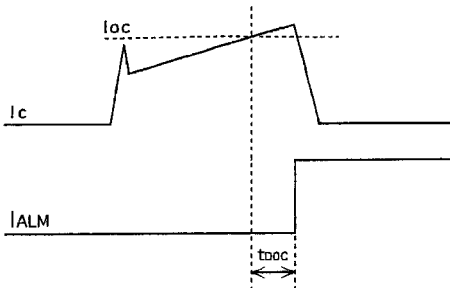


Fig.2 Definition of OC delay time

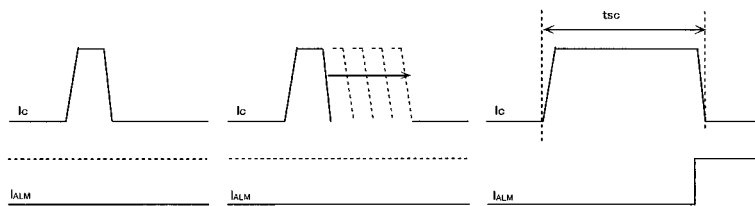


Fig.3 Definition of t_{sc}

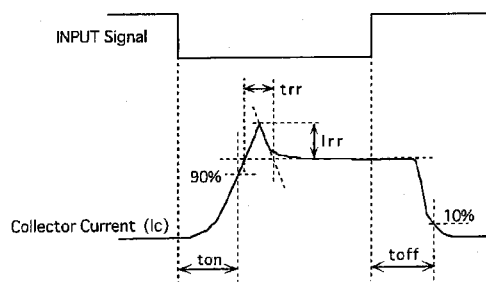


Fig.4 Definition of switching time

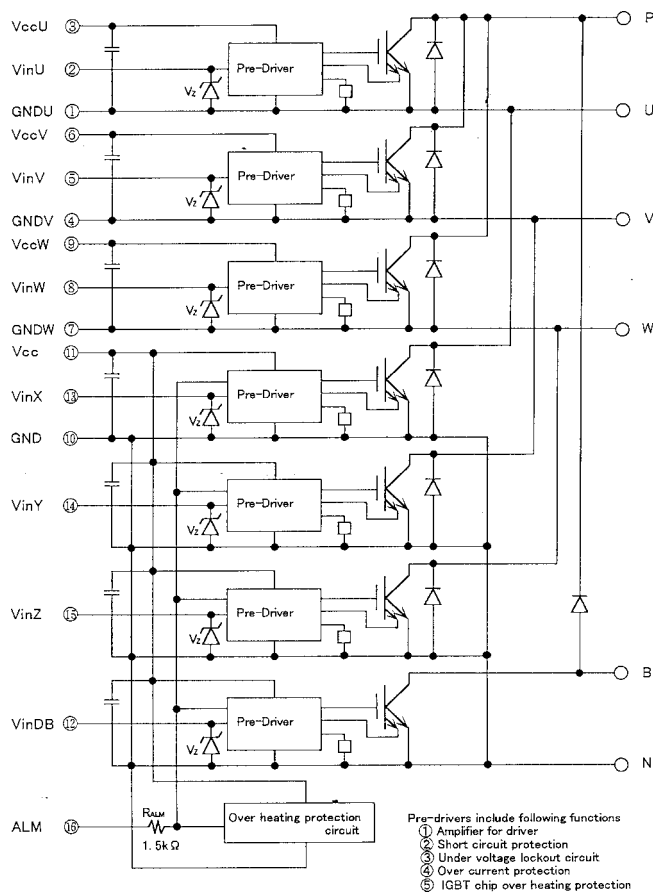
● Thermal characteristics($T_c=25^\circ\text{C}$)

| Item | Symbol | Typ. | Max. | Unit | | |
|--|---------------|------|---------------|--------------------|------|--------------------|
| Junction to Case thermal resistance | INV | IGBT | $R_{th(j-c)}$ | - | 0.12 | $^\circ\text{C/W}$ |
| | | FWD | $R_{th(j-c)}$ | - | 0.25 | $^\circ\text{C/W}$ |
| | DB | IGBT | $R_{th(j-c)}$ | - | 0.31 | $^\circ\text{C/W}$ |
| Case to fin thermal resistance with compound | $R_{th(c-f)}$ | 0.05 | - | $^\circ\text{C/W}$ | | |

● Recommendable value

| Item | Symbol | Min. | Typ. | Max. | Unit | |
|--|---------------|------|------|------|------|-----|
| DC bus voltage | V_{DC} | 200 | - | 400 | V | |
| Operating power supply voltage range of Pre-driver | V_{CC} | 13.5 | 15 | 16.5 | V | |
| Switching frequency of IPM | f_{sw} | 1 | - | 20 | kHz | |
| Screw torque | Mounting (M5) | - | 2.5 | - | 3.0 | N·m |
| | Terminal (M5) | - | 2.5 | - | 3.0 | N·m |

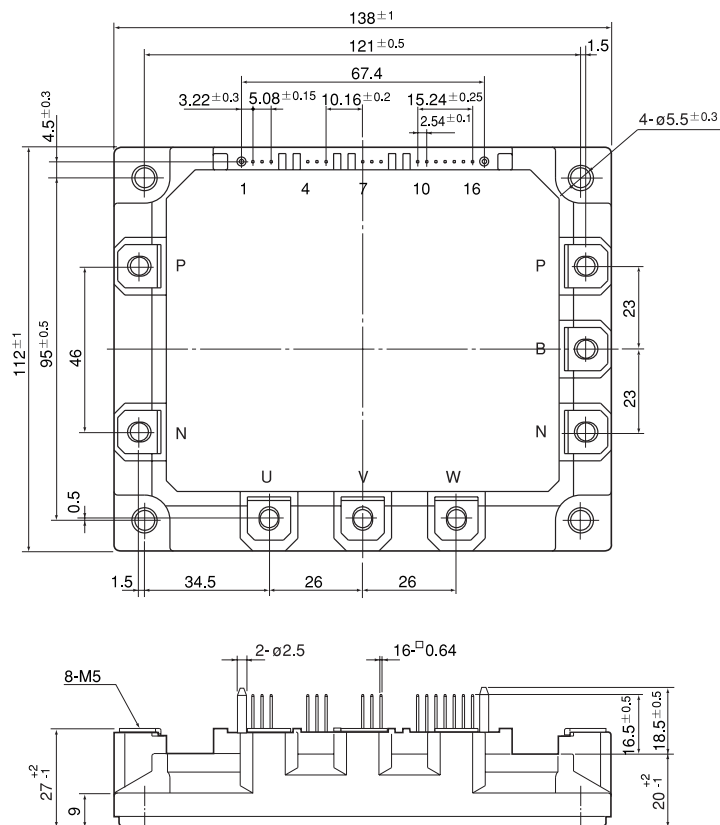
Block diagram



Pre-drivers include following functions
 a) Amplifier for driver
 b) Short circuit protection
 c) Undervoltage lockout circuit
 d) Over current protection
 e) IGBT chip over heating protection

Pre-drivers include following functions
 ① Amplifier for driver
 ② Short circuit protection
 ③ Undervoltage lockout circuit
 ④ Over current protection
 ⑤ IGBT chip over heating protection

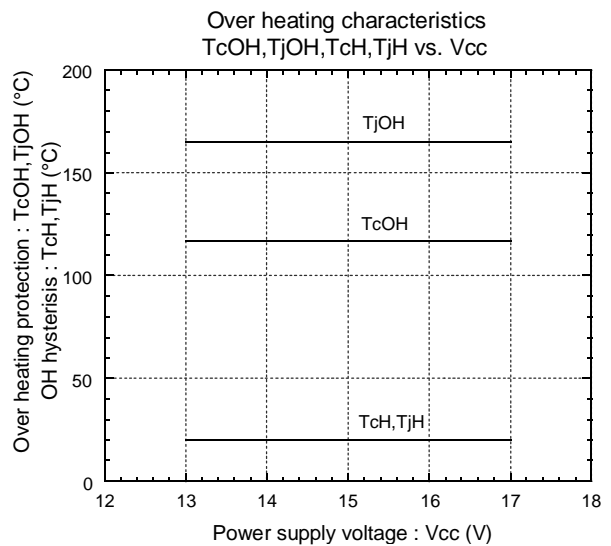
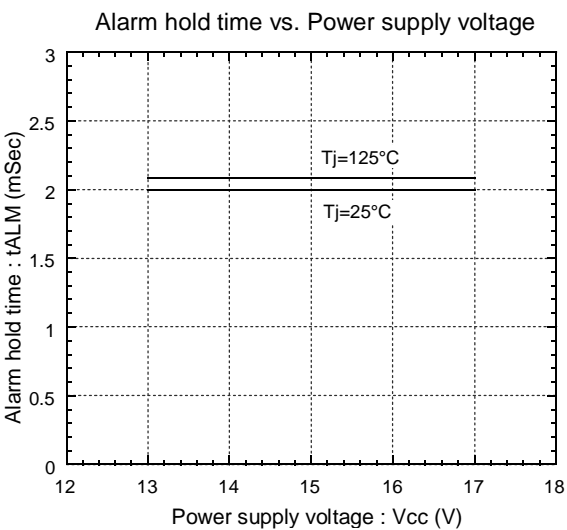
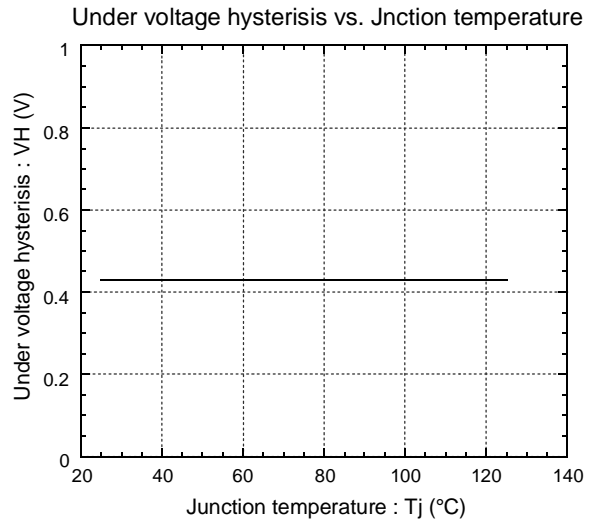
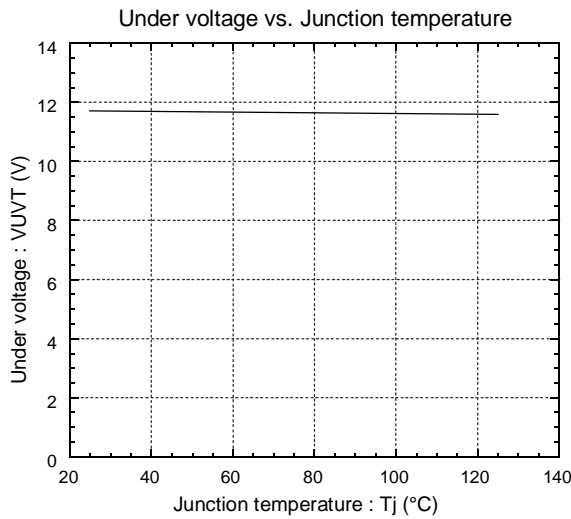
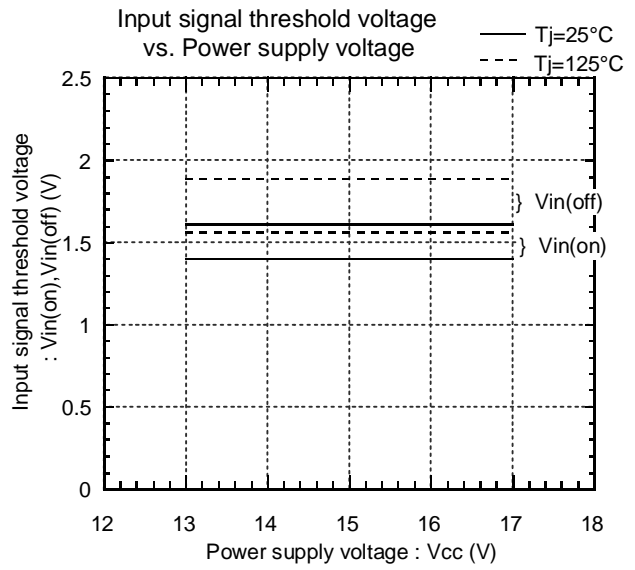
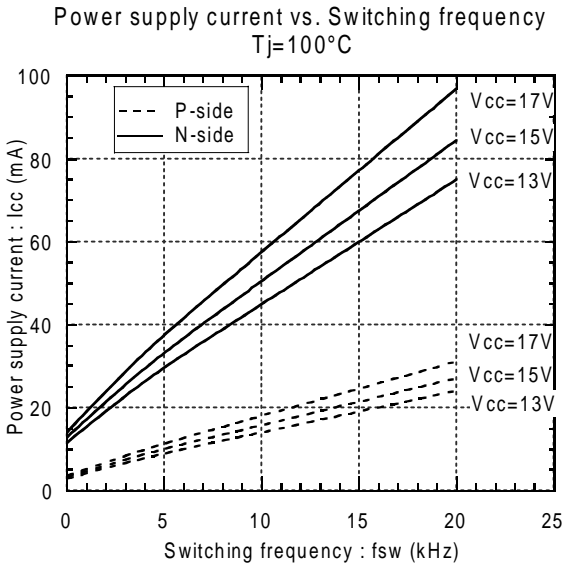
Outline drawings, mm



Mass : 920g

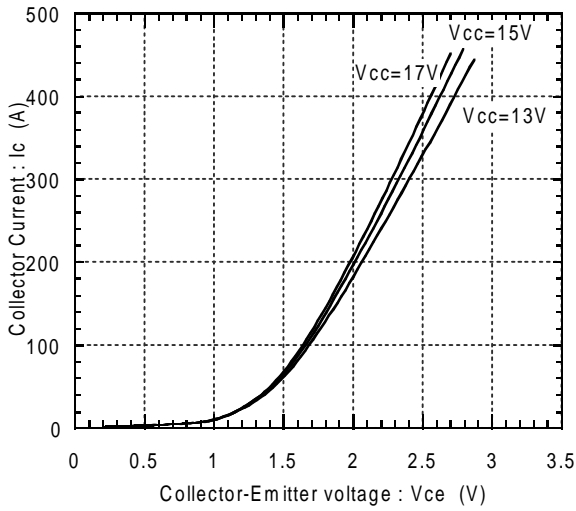
■ Characteristics (Representative)

● Control circuit

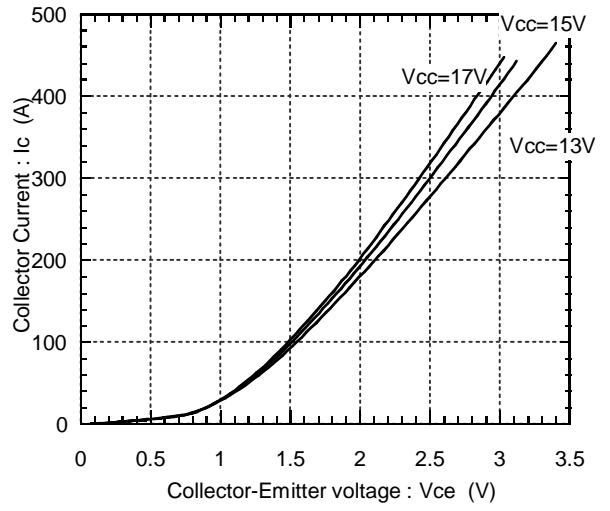


● Inverter

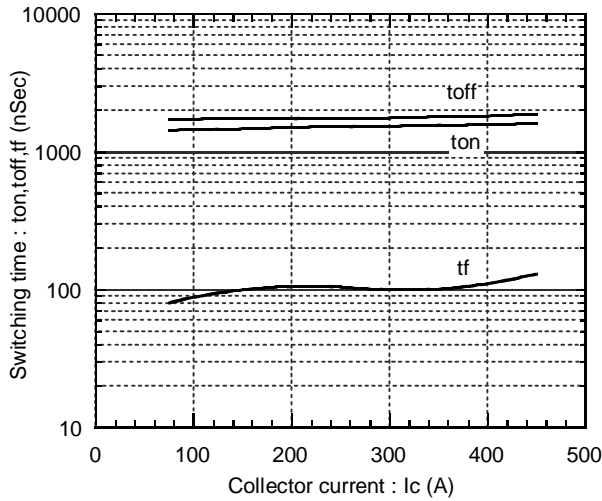
Collector current vs. Collector-Emitter voltage
T_j=25°C



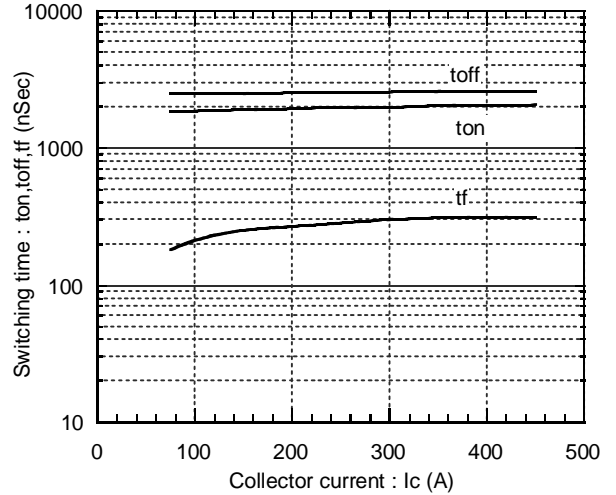
Collector current vs. Collector-Emitter voltage
T_j=125°C



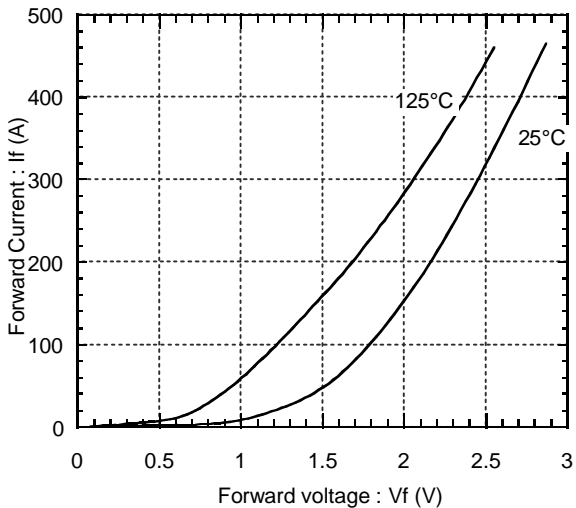
Switching time vs. Collector current
E_{dc}=300V, V_{cc}=15V, T_j=25°C



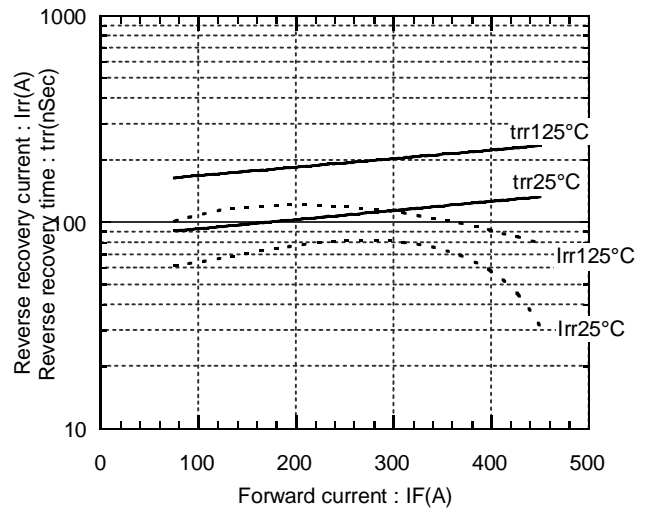
Switching time vs. Collector current
E_{dc}=300V, V_{cc}=15V, T_j=125°C



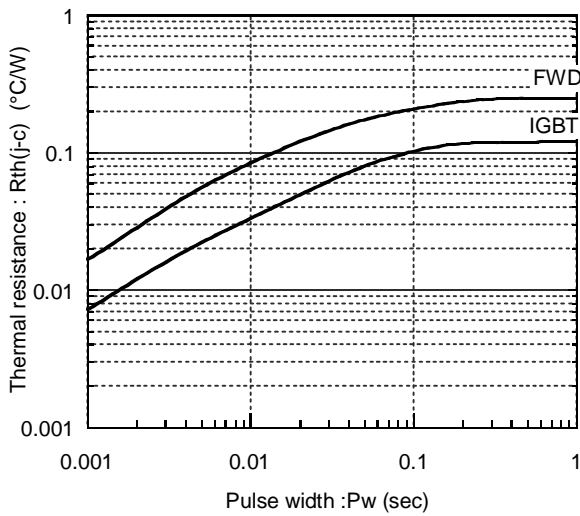
Forward current vs. Forward voltage



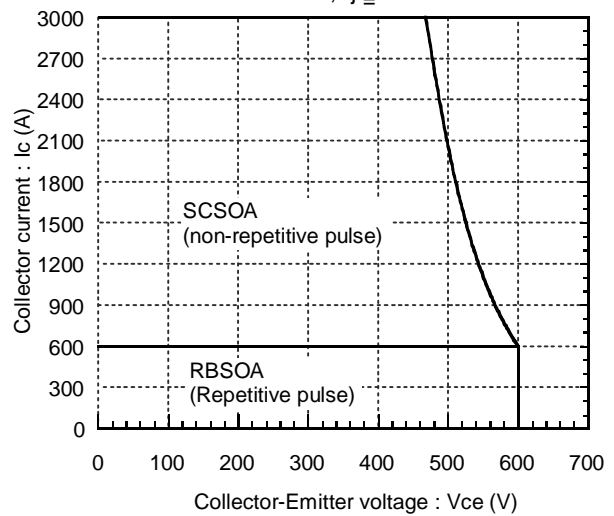
Reverse recovery characteristics
trr, Irr vs. IF



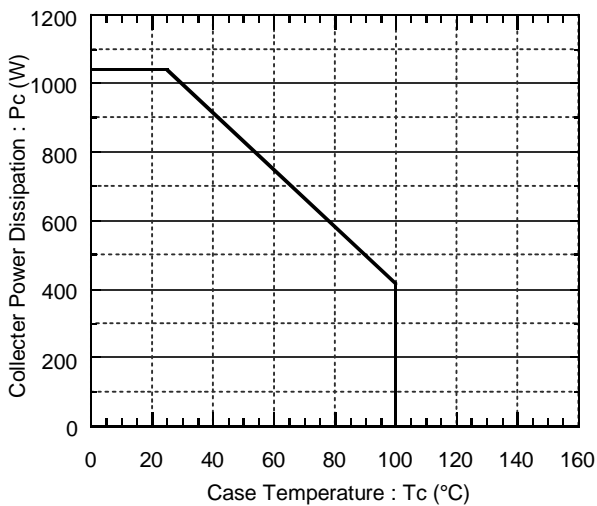
Transient thermal resistance



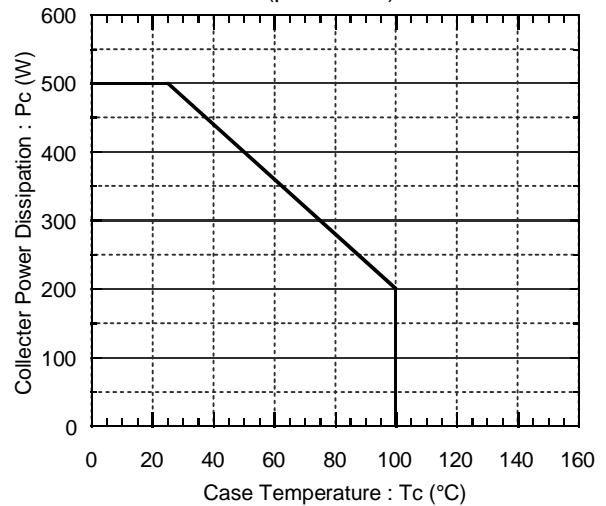
Reversed biased safe operating area
Vcc=15V, Tj ≤ 125°C



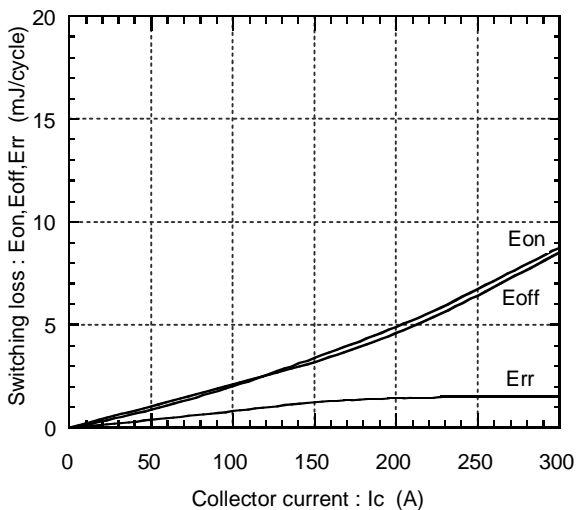
Power derating for IGBT
(per device)



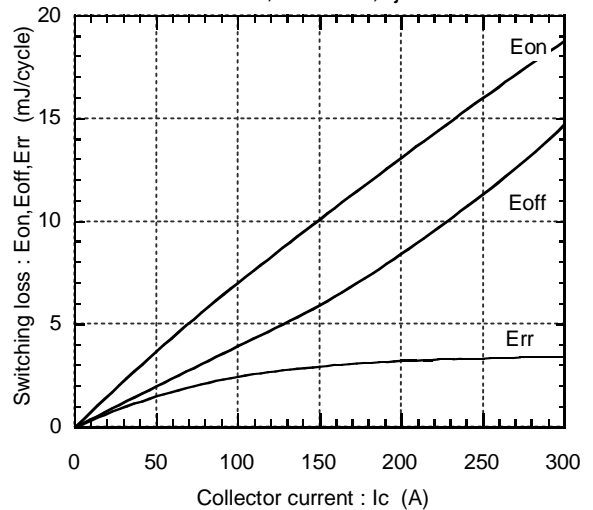
Power derating for FWD
(per device)

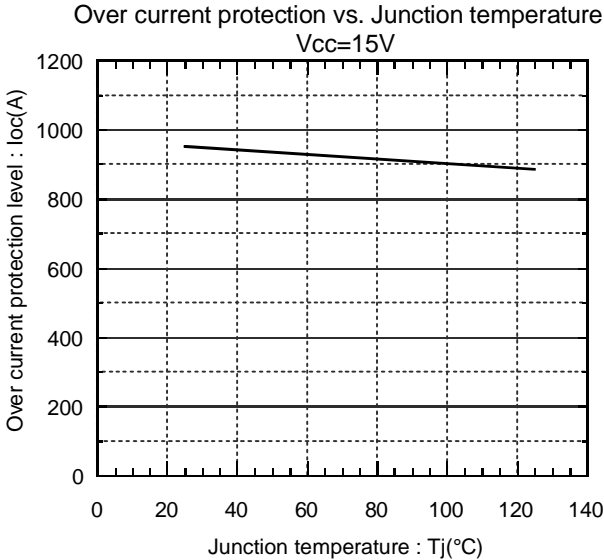


Switching Loss vs. Collector Current
Edc=300V, Vcc=15V, Tj=25°C



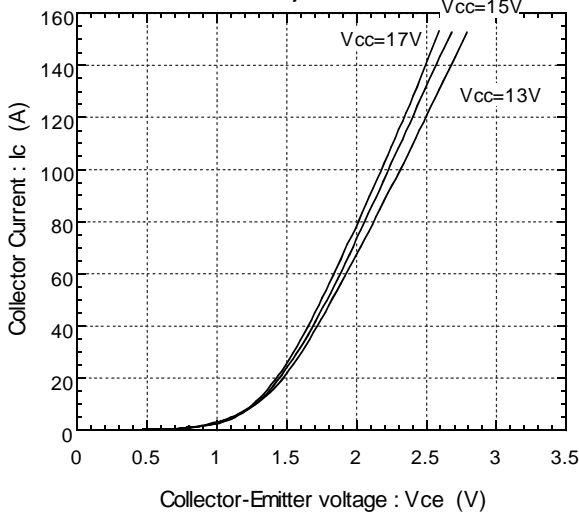
Switching Loss vs. Collector Current
Edc=300V, Vcc=15V, Tj=125°C



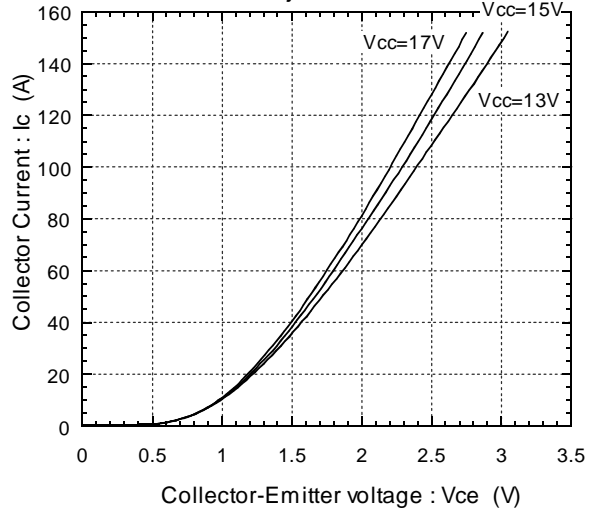


● Brake

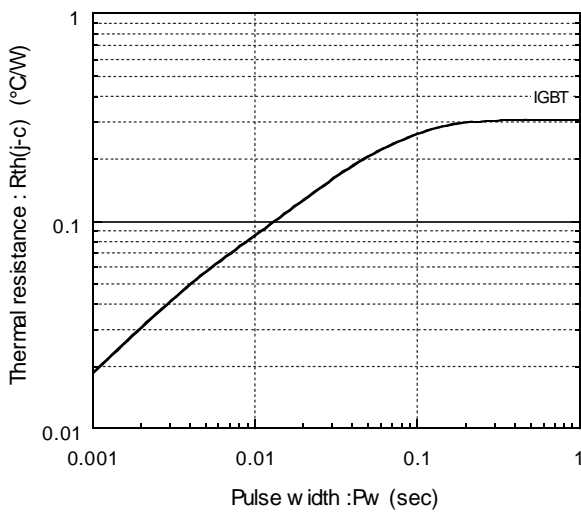
Collector current vs. Collector-Emitter voltage
T_j=25°C



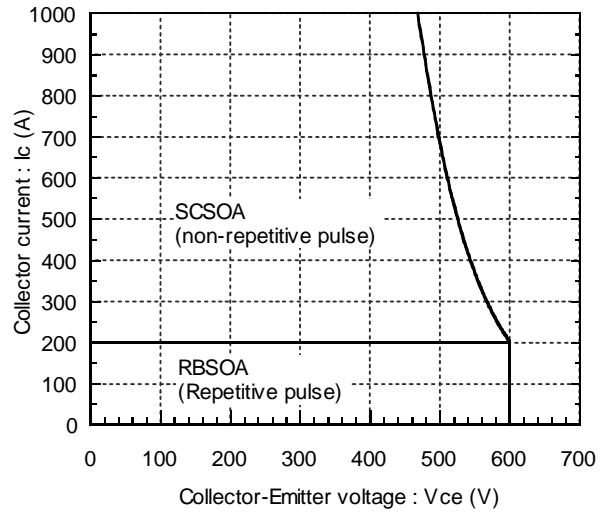
Collector current vs. Collector-Emitter voltage
T_j=125°C



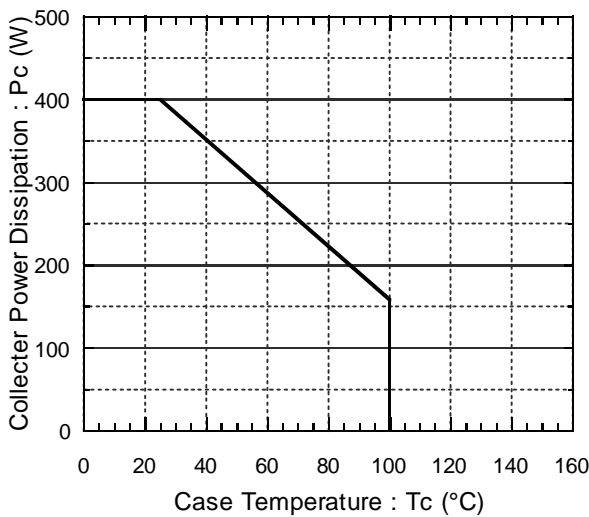
Transient thermal resistance



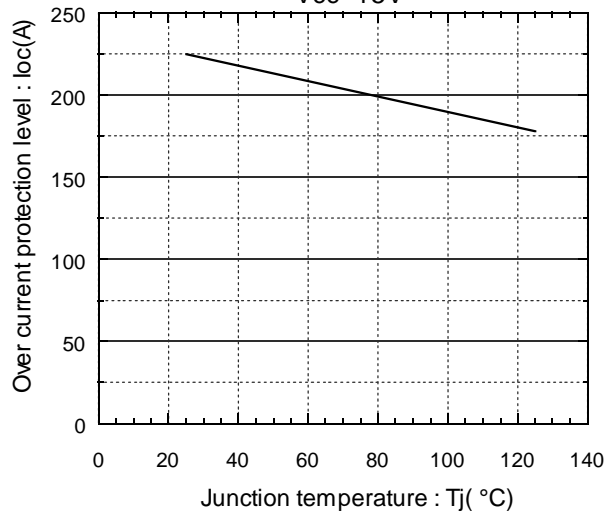
Reversed biased safe operating area
V_{cc}=15V, T_j ≤ 125°C



Power derating for IGBT
(per device)



Over current protection vs. Junction temperature
V_{cc}=15V





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